

# UTC MPSA42/43 NPN EPITAXIAL SILICON TRANSISTOR

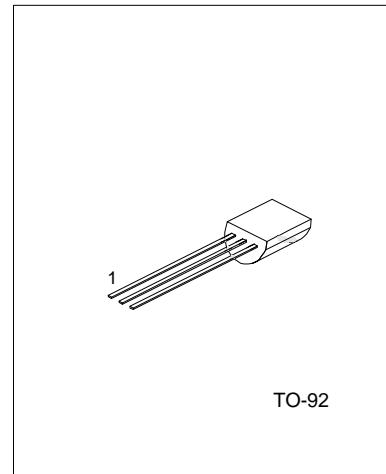
## HIGH VOLTAGE TRANSISTOR

### DESCRIPTION

The UTC MPSA42/43 are high voltage transistors, designed for telephone switch and high voltage switch.

### FEATURES

- \*Collector-Emitter voltage:
  - V<sub>CEO</sub>=300V(UTC MPSA42)
  - V<sub>CEO</sub>=200V(UTC MPSA43)
- \*High current gain
- \*Complement to UTC MPSA92/93
- \*Collector Dissipation:
  - P<sub>c</sub>(max)=625mW



1:EMITTER 2:BASE 3:COLLECTOR

### ABSOLUTE MAXIMUM RATINGS ( Operating temperature range applies unless otherwise specified )

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage UTC MPSA42 UTC MPSA43	V <sub>CBO</sub>	300	V
		200	
Collector-Emitter Voltage UTC MPSA42 UTC MPSA43	V <sub>CCEO</sub>	300	V
		200	
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Dissipation	P <sub>c</sub>	625	mW
Collector Current	I <sub>c</sub>	500	mA
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### ELECTRICAL CHARACTERISTICS(T<sub>j</sub>=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage UTC MPSA42 UTC MPSA43	BV <sub>CBO</sub>	I <sub>c</sub> =100μA,I <sub>E</sub> =0	300			V
			200			
Collector-Emitter Breakdown Voltage UTC MPSA42 UTC MPSA43	BV <sub>CCEO</sub>	I <sub>c</sub> =1mA,I <sub>B</sub> =0	300			V
			200			
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =100μA,I <sub>c</sub> =0	6			V
Collector Cut-Off Current UTC MPSA42 UTC MPSA43	I <sub>CBO</sub>	V <sub>CB</sub> =200V,I <sub>E</sub> =0 V <sub>CB</sub> =160V,I <sub>E</sub> =0		100	100	nA
Emitter Cut-Off Current UTC MPSA42 UTC MPSA43	I <sub>EBO</sub>	V <sub>BE</sub> =6V,I <sub>c</sub> =0 V <sub>BE</sub> =4V,I <sub>c</sub> =0		100	100	nA

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC Current Gain(note)	$h_{FE}$	$V_{CE}=10V, I_c=1mA$ $V_{CE}=10V, I_c=10mA$ $V_{CE}=10V, I_c=30mA$	80 80 80		300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=20mA, I_b=2mA$			0.2	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c=20mA, I_b=2mA$			0.90	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=20V, I_c=10mA, f=100MHz$	50			MHz
Collector Base Capacitance UTC MPSA42 UTC MPSA43	$C_{cb}$	$V_{CB}=20V, I_E=0$ $f=1MHz$			3 4	pF

## TYPICAL PERFORMANCE CHARACTERISTICS

Fig.1 DC Current Gain

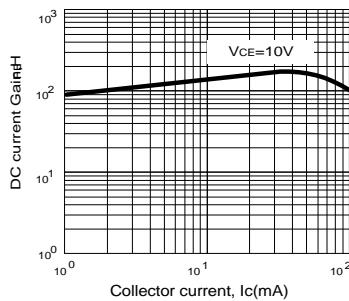


Fig.2 Saturation Voltage

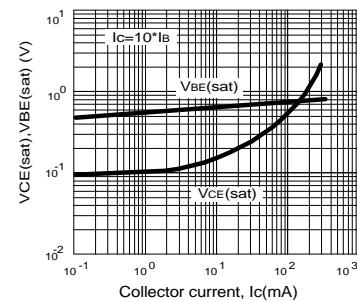


Fig.3 Capacitance

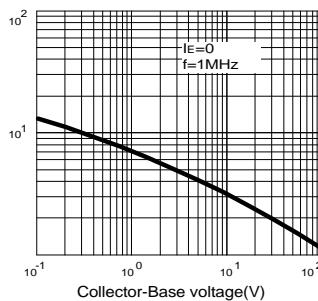


Fig.4 Current Gain Bandwidth product

